

## AMENDMENTS TO THE CLAIMS

1. (Cancelled)

2. (Currently Amended) An alternating phase-shifting lithographic mask comprising:

a plurality of 0 degree phase-shifting regions; and  
a plurality of corresponding 180 degree phase-shifting regions, wherein a first set of the 180 degree phase-shifting regions includes a first bias and a second set of the 180 degree phase-shifting regions includes a second bias ~~The alternating phase-shifting lithographic mask of Claim 1,~~ wherein the first set includes optical proximity correction that minimizes changes to the first bias and the second set includes optical proximity correction that minimizes changes to the second bias, wherein at least one of the 180 degree phase-shifting regions comprises multiple regions in which at least two regions have different phase or transmission.

3. (Cancelled)

4. (Currently Amended) A lithographic mask that provides phase-shifting for features on a binary mask, the lithographic mask comprising:

a plurality of first phase-shifting regions; and  
a plurality of second phase-shifting regions,  
wherein each first phase-shifting region has a corresponding second phase-shifting region,  
wherein a phase difference between the first and second phase-shifting regions is approximately 180 degrees,  
wherein each second phase-shifting region has a size based on a size of its corresponding first phase-shifting region ~~The~~

~~lithographic mask of Claim 3~~, wherein at least one of the plurality of first phase-shifting regions and the plurality of second phase-shifting regions include optical proximity correction, wherein at least one of the second phase-shifting regions comprises multiple regions in which at least two regions have different phase or transmission.

5. (Cancelled)